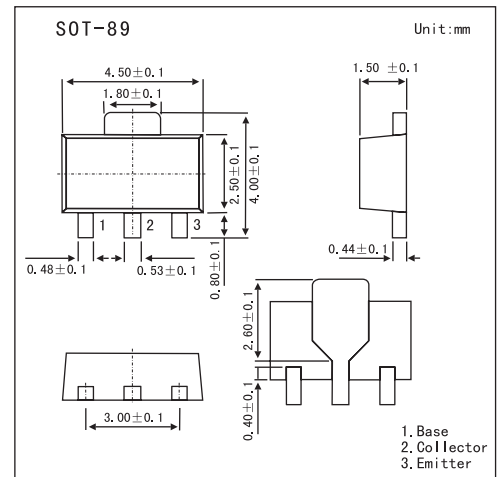


## Silicon NPN Epitaxial Planar Type

## 2SD2357

## ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$ .
- Large collector power dissipation  $P_c$ .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	10	V
Collector-emitter voltage	$V_{CE0}$	10	V
Emitter-base voltage	$V_{EB0}$	5	V
Collector current	$I_c$	1.2	A
Peak collector current	$I_{CP}$	1	A
Collector power dissipation	$P_c$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base cutoff current	$I_{CBO}$	$V_{CB} = 7\text{ V}, I_E = 0$			1	$\mu\text{A}$
Collector-base voltage	$V_{CB0}$	$I_c = 10\ \mu\text{A}, I_E = 0$	10			V
Collector-emitter voltage	$V_{CE0}$	$I_c = 1\ \text{mA}, I_B = 0$	10			V
Emitter-base voltage	$V_{EB0}$	$I_E = 10\ \mu\text{A}, I_c = 0$	5			V
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 2\ \text{V}, I_c = 100\ \text{mA}$	200		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 500\ \text{mA}, I_B = 5\ \text{mA}$			0.15	V
Transition frequency	$f_T$	$V_{CB} = 5\ \text{V}, I_E = -50\ \text{mA}, f = 200\ \text{MHz}$		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 5\ \text{V}, I_E = 0, f = 1\ \text{MHz}$		30		pF

## ■ Marking

Marking	1M
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